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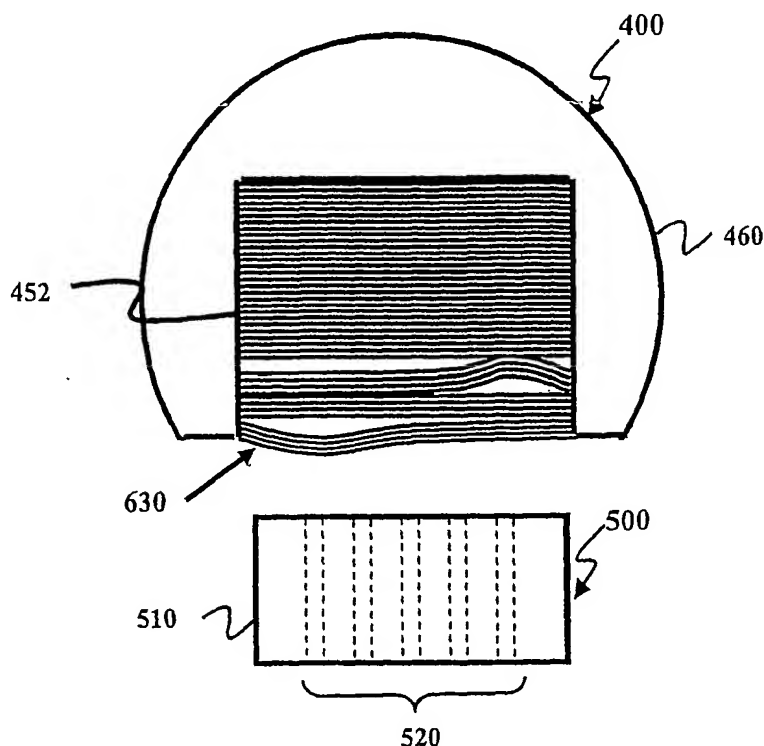
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[Continued on next page]

(54) Title: SEPARATING AND ASSEMBLING SEMICONDUCTOR STRIPS



(57) Abstract: A method and an apparatus for separating elongated semiconductor strips (630) from a wafer (400) of semiconductor material are disclosed. Vacuum (500) is applied to the face of each semiconductor strip forming an edge of the wafer (400) or being adjacent to the edge. The wafer (400) and the source of the vacuum (500) are displaced to separate each elongated semiconductor strip (630) from the wafer (400). Further, a method and an apparatus for assembling elongated semiconductor strips (630) separated from a wafer (400) of semiconductor material into an array of strips (630) are disclosed. Still further, methods, apparatuses, and systems for assembling an array of elongated semiconductor strips (630) on a substrate are also disclosed.



SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

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